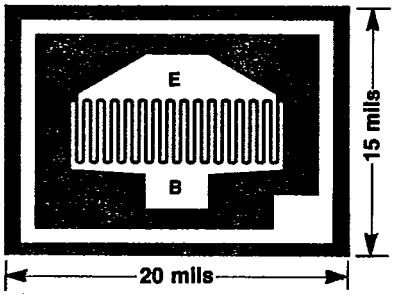
DIE NO. 2C5583 — PNP
LINE SOURCE — RF502.59

This die provides performance equal to or better than that of the following device types:

2N5583

High-frequency low-to-medium power PNP transistor designed for class A, B and C amplifiers, oscillators, mixers, multipliers and high-speed switches in the 1-1000 MHz frequency range.

- $f_T \leq 1.3$ GHz @ 10V/100 mA



Backside Collector

METALLIZATION —
Top ..... Al
Back ..... Au
BACKSIDE GOLD 3000Å
DIE THICKNESS ..... 6 ± 2 mils
BONDING PAD SIZE —
Emitter ..... 2.2 x 3.2 mils
Base ..... 2.2 x 3.3 mils

ELECTRICAL CHARACTERISTICS (T_A = 25°C, Note 1)

Parameter	Test Conditions	Min	Max	Unit
BV_{CEO}	I_C = 10 mAdc	30	—	Vdc
BV_{CBO}	I_C = 10 μAdc	30	—	Vdc
BV_{EBO}	I_E = 100 μAdc	3.0	—	Vdc
I_{CBO}	V_{CB} = 20 Vdc	—	50	nAdc
h_{FE1}	V_{CE} = 2.0 Vdc, I_C = 40 mAdc	20	—	—
h_{FE2}	V_{CE} = 2.0 Vdc, I_C = 100 mAdc	25	100	—
h_{FE3}	V_{CE} = 5.0 Vdc, I_C = 300 mAdc	15	—	—
$V_{CE\ (sat)}$	I_C = 100 mAdc, I_B = 10 mAdc	—	0.8	Vdc

NOTES:
1. Because of the limitations of probe testing, only dc parameters are tested. These parameters must be measured using pulse techniques: pulse width ≤ 300 μs, duty cycle ≤ 2%.
2. Detailed device characteristics are available from your Motorola sales representative.